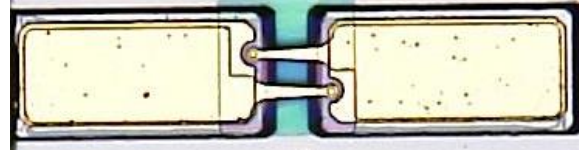


# Anti-parallel Air-bridged Schottky Diodes

## *GaAs varistor diodes*



### Features

- Gold air-bridged structure
- Passivated or non-passivated anode and finger
- Very low parasitic capacitance
- Low series resistance
- 100% electrically tested
- 100% visual inspection

Part number	Anode area ( $\mu\text{m}^2$ )	Junction capacitance (fF)
AP1/G2/0P95	0.95	1.42
AP1/G2/1P54	1.54	2.29
AP1/G2/2P27	2.27	3.38
AP1/G2/3P14	3.14	4.68
AP1/G2/3P80	3.80	5.66
AP1/G2/4P15	4.16	6.19
AP1/G2/5P31	5.31	7.91
AP1/G2/6P60	6.60	9.84

### Chip parameters

Parameter	Unit	Min.	Typ.	Max.
Chip length	$\mu\text{m}$	163	173	183
Chip width	$\mu\text{m}$	44	54	64
Chip thickness	$\mu\text{m}$	13	15	17

### Part Number Guide

**XXN / NYN / NNPN**

Diode configuration		Chip details			Anode
Diode series	Series number	Number of anodes	Substrate material	Schottky doping density $\times 10^{17}\text{cm}^{-3}$	Anode area $\mu\text{m}^2$

To order these diodes please contact [sales@teratechcomponents.com](mailto:sales@teratechcomponents.com)  
[www.teratechcomponents.com](http://www.teratechcomponents.com)